

3. (Amended) A liquid crystal panel substrate comprising:

B<sup>2</sup>  
a pixel region having a matrix of reflecting electrodes formed on a substrate and a switching element formed corresponding to each of said reflecting electrodes, a periphery region of said pixel region on the substrate having at least insulating interlayers; and

a passivation film having a laminate structure comprising a silicon oxide film and a silicon nitride film on said silicon oxide film, the passivation film being formed at least on a side of edge sections of the at least insulating interlayers.

4. (Amended) A liquid crystal panel substrate comprising:

a pixel region having a matrix of reflecting electrodes formed on a substrate and a transistor formed corresponding to each of the reflecting electrodes;

a peripheral circuit arranged in a periphery region of said pixel region on the substrate for supplying signals to said transistors in said pixel region;

a first passivation film comprising a silicon oxide film formed on said reflecting electrodes in said pixel region; and

a second passivation film comprising a silicon nitride film formed at least on a side of edge sections of said periphery region.

- B<sup>3</sup>  
9. (Amended) A liquid crystal panel substrate according to claim 3, said edge section of said insulating interlayers being a scribed region of the substrate.

Please add new claims 14 and 15 as follows: /

- B<sup>4</sup>  
--14. A liquid crystal panel substrate, comprising:

reflecting electrodes formed on a substrate;

a switching element formed corresponding to each of the reflecting electrodes;

a passivation film formed on the reflecting electrodes comprising a silicon oxide film; and

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a silicon nitride film formed as an insulating interlayer between the reflecting electrodes and the switching element so as to cover the switching element except for a connection portion between the reflecting electrode and the switching element.--

--15. The liquid crystal substrate according to claim 7, the second silicon oxide layer being the same layer as the first silicon oxide layer.--

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REMARKS

Claims 1-15 are pending. By this Amendment, claims 1, 3, 4 and 9 are amended and claims 14 and 15 are added. Reconsideration based on the following remarks is respectfully requested.

The attached Appendix includes marked-up copies of each rewritten claim (37 C.F.R. §1.121(c)(1)(ii)).

Applicant gratefully acknowledges that the Office Action indicates that claims 7, 12 and 13 are allowable.

**I. THE CLAIMS DEFINE PATENTABLE SUBJECT MATTER**

The Office Action rejects claim 1 under 35 U.S.C. §103(a) as unpatentable over U.S. Patent No. 5,767,827 to Kobayashi et al. ("Kobayashi") in view of U.S. Patent No. 5,805,252 to Shimada et al. ("Shimada"); claim 2 under 35 U.S.C. §103(a) as unpatentable over Kobayashi and Shimada in view of U.S. Patent No. 5,056,895 to Kahn ("Kahn"); claims 3, 8 and 9 under 35 U.S.C. §103(a) as unpatentable over U.S. Patent No. 5,510,918 to Matsunaga et al. ("Matsunaga") in view of Kahn; claim 4 under 35 U.S.C. §103(a) as unpatentable over Kobayashi in view of Matsunaga; claim 5 under 35 U.S.C. §103(a) as unpatentable over Kobayashi in view of Shimada; claim 6 under 35 U.S.C. §103(a) as unpatentable over Kobayashi in view of Kahn; and claims 10 and 11 under 35 U.S.C. §103(a) as unpatentable over Matsunaga in view of Kahn. These rejections are respectfully traversed.